研究成果報告書 科学研究費助成事業



今和 4 年 4 月 2 6 日現在

機関番号: 32717 研究種目: 若手研究 研究期間: 2020~2021

課題番号: 20K15385

研究課題名(和文) Developing novel p-type BiOX oxyhalides thin layer for stable and efficient CsPbI3 perovskite solar cells

研究課題名(英文) Developing novel p-type BiOX oxyhalides thin layer for stable and efficient CsPb13 perovskite solar cells

研究代表者

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交付決定額(研究期間全体):(直接経費) 3,200,000円

研究成果の概要(和文):このプロジェクトは、効率的で安定したCsPbX3ペロブスカイト太陽電池(PSC)の開発を目指しており、以下の結果が得られました。アモルファスSnOxとドーパントフリーポリマーPDTDTの電荷輸送材料を開発しました。これにより、CsPbX3 PSCの高効率、特に高電圧、および優れた安定性が実現されました。CsPbX3欠陥(配位不足のPb2+と金属Pb)は、分子表面パッシベーション法によって抑制され、電圧を理論限界の92%以上に高めました。これらの研究は、電圧を上げることによってCsPbX3 PSCの低効率の問題を解決しました。安定性も、PDTDTを使用することで改善され ました。

研究成果の学術的意義や社会的意義この研究は、CsPbX3太陽電池の電圧損失と不安定性の問題を解決しました。 その結果、タンデム太陽電池や屋内太陽光発電への応用がより有望になります。 トップセルとしてCsPbX3を使用すると、タンデム太陽電池で2 Vを超える高電圧と30%を超える効率が達成さ

れ、Siパネルよりも効率的な太陽電池を提供できます。 十分な電力と駆動電圧を提供するCsPbX3屋内太陽電池を使用することで、セルフパワーのIoTシステムを実現できます。

研究成果の概要(英文): CsPbX3 (X=I, Br) perovskite solar cells (PSCs) have potential applications in tandem solar cells and indoor photovoltaics. While the low efficiency and poor stability are limiting their perspectives. This project is aiming at developing efficient and stable CsPbX3 PSCs and the following results were achieved.

Firstly, charge transport materials of amorphous SnOx and dopant-free polymer PDTDT were developed, by which the high efficiency especially the high voltage, and good stability of CsPbX3 PSCs were realized. These materials can be used in other research on CsPbX3 PSCs. Secondly, the CsPbX3 perovskite defects (undercoordinated Pb2+ and metallic Pb) were well suppressed by a molecule surface passivation method, promoting the voltage of solar cells to over 92% of the theoretical limit. In summary, these researches solved the problem of the low efficiency of CsPbX3 PSCs by increasing the voltage. The stability of CsPbX3 PSCs was also improved by using the dopant-free PDTDT.

研究分野:ペロブスカイト太陽電池

キーワード: ペロブスカイト太陽電池 全無機ペロブスカイト 高電圧

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1.研究開始当初の背景

CsPbX₃ perovskite solar cells (PSCs) have application potential in tandem solar cells and indoor photovoltaics. While their low efficiency and poor stability are limiting their perspectives.

- (1) The low efficiency is mainly because of the low Voc. For CsPbX₃ PSCs, the photocurrent is approaching the theoretical limit and the fill factor is always high in most reported cases. While the Voc is still quite low and most of the reported Voc values are only 80% of the theoretical limits, leaving big space to improve.
- (2) The poor stability of CsPbX₃ is mainly because the perovskite phase is unstable against humidity and easily transforms into a non-perovskite phase. The dopants of widely used hole transport material (HTM), Spiro-MeOTAD, can absorb humidity and trigger the perovskite phase transition, damaging the performance of CsPbX₃ solar cells. Therefore, improving Voc for enhancing the device efficiency and developing dopant-free HTMs are important topics for CsPbX₃ solar cells.

2.研究の目的

This project aims to improve the efficiency and stability of CsPbX₃ PSCs.

3. 研究の方法

- (1) For improving the efficiency, proper charge transport materials were developed for $CsPbX_3$ and the perovskite defects were suppressed by a molecule passivation engineering.
- (2) For enhancing the stability, a p-type polymer was developed and used as a dopant-free HTM to avoid the hygroscopic dopant-induced perovskite phase transition.

4. 研究成果

(1) The conventional charge transport materials such as TiO₂ and Spiro-OMeTAD are suitable for hybrid perovskites while not perfect for CsPbX₃. The main reason is the mismatch of the energy levels between these materials and CsPbX₃, which will lead to large energy loss at the interface and result in low Voc and efficiency. For solving this problem, on one hand, an amorphous SnOx electron transport layer (ETL) and PDTDT polymer HTM were developed. The SnOx has a slightly higher conduction band than that of perovskite, forming an interfacial spike structure, which can efficiently prevent the electron backtransfer and electron-hole nonradiative recombination. The SnOx layer remarkably improved the Voc of CsPbI2Br solar cells to 1.42 V (Figure 1), which is much higher than everreported values. With enhanced Voc, an efficiency of 15.53% was obtained.

On other hand, a p-type polymer PDTDT was synthesized and used as HTM. This polymer has a proper HOMO level of -5.44 eV, which is lower than Spiro-OMeTAD and matches well with the valence band position of CsPbI₂Br (-5.77 eV). It also has high hole mobility and the casted film shows a face-on orientation, both of which are beneficial for the hole transfer. When used as a dopant-free HTM, a record-high efficiency of 17.36% was achieved for CsPbI₂Br solar cells (Figure 2).

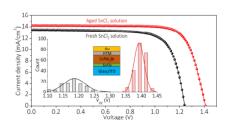


Figure 1. J-V curves of CsPbI₂Br solar cells employing SnOx ETL prepared using fresh and aged SnCl₂ solution.

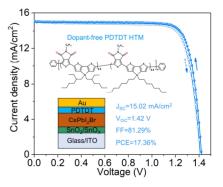


Figure 2. J-V curve of $CsPbI_2Br$ solar cells employing PDTDT as HTM.

(2) As a type of solution-processed material, perovskite film always has various kinds of defects that are bad for the device's performance. Compared with bulk defects, the perovskite surface defect property is more decisive to the performance. In this part, the surface defect property of CsPbX₃ was studied using density functional theory calculations and iodine vacancy was found to be the main type of defect. For reducing the iodine vacancy, i.e., undercoordinated Pb²⁺, a thiophene-based molecule was used for surface passivation. It was found that the thiophene unit has strong interaction with Pb²⁺, which well suppressed the iodine vacancies and the metallic Pb defects. As a result, the Voc of CsPbI_{2.25}Br_{0.75} solar cells was improved from 1.36 to 1.42 V, leading to the efficiency

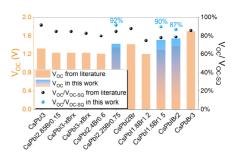


Figure 3. Summary of Voc and its ratio to S-Q limit for CsPbX₃ solar cells reported in literature and achieved this work.

enhancement from 15.55 to 16.72%. The Voc of 1.42 V is reaching 92% of the theoretical limit of a 1.86 eV $CsPbI_{2.25}Br_{0.75}$ perovskite, which is higher than those in reported $CsPbX_3$ solar cells (Figure 3). This method also improved the Voc of other compositional $CsPbX_3$ solar cells, such as from 1.42 to 1.51 V (90% of limit) for $CsPbI_{1.5}Br_{1.5}$ (1.99 eV) and from 1.44 to 1.54 V (87% of limit) for $CsPbIBr_2$ (2.10 eV) solar cells, implying its universality.

(3) CsPbX₃ perovskites have an issue of poor phase stability because their perovskite phase can easily transform to a non-perovskite phase when exposed to humidity. While the widely used Spiro-OMeTAD HTM can only work efficiently with the help of hygroscopic dopants. These dopants easily absorb the moisture and trigger the perovskite phase transition, which will degrade the perovskite material stability and the device's performance. For solving this problem, the developed PDTDT polymer was used as dopant-free HTM. Except for the recordhigh efficiency of 17.36% achieved using this polymer (Figure 2), its effect on the stability of CsPbI₂Br was studied. It was

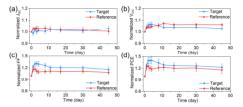


Figure 4. Long-term stability of CsPbI₂Br solar cells employing PDTDT (target) and P3HT (reference) as HTM.

found that while Spiro-OMeTAD degraded the perovskite phase in a short time, the PDTDT-based device showed good long-term stability. The PDTDT-based samples were stored in an environment with 10-20% humidity and measured efficiency in a 20% humidity condition. After 45 days, the samples still keep 88% of the champion values (Figure 4), indicating the positive role of PDTDT in maintaining the perovskite phase and the device performance.

In summary, in this project, the efficiency of CsPbX₃ solar cells was improved by remarkably enhancing the Voc through the engineering of developing suitable charger transport materials and perovskite surface passivation. The stability of CsPbX₃ solar cells was improved by employing dopant-free polymer to replace the conventional HTM of Spiro-OMeTAD (with dopants) for avoiding the perovskite phase transition.

< 引用文献 >

- (1) Zhanglin Guo*, Ajay Kumar Jena, Izuru Takei, Gyu Min Kim, Muhammad Akmal Kamarudin, Yoshitaka Sanehira, Ayumi Ishii, Youhei Numata, Shuzi Hayase, and Tsutomu Miyasaka*, *Journal of the American Chemical Society*, 2020, 142, 21, 9725-9734.
- (2) Zhanglin Guo*, Ajay Kumar Jena, Izuru Takei, Masashi Ikegami, Ayumi Ishii, Youhei Numata, Naoyuki Shibayama, Tsutomu Miyasaka*, *Advanced Functional Materials*, 2021: 2103614.

5 . 主な発表論文等

【雑誌論文】 計2件(うち査読付論文 2件/うち国際共著 0件/うちオープンアクセス 0件)

4 . 巻
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5 . 発行年
2021年
6.最初と最後の頁
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1. 著者名	4 . 巻
Guo Zhanglin, Jena Ajay Kumar, Takei Izuru, Kim Gyu Min, Kamarudin Muhammad Akmal, Sanehira	142
Yoshitaka, Ishii Ayumi, Numata Youhei, Hayase Shuzi, Miyasaka Tsutomu	
2.論文標題	5 . 発行年
VOC Over 1.4 V for Amorphous Tin-Oxide-Based Dopant-Free CsPb12Br Perovskite Solar Cells	2020年
3 . 雑誌名	6.最初と最後の頁
Journal of the American Chemical Society	9725-9734
掲載論文のDOI(デジタルオブジェクト識別子)	査読の有無
10.1021/jacs.0c02227	有
オープンアクセス	国際共著
オープンアクセスではない、又はオープンアクセスが困難	-

〔学会発表〕 計4件(うち招待講演 1件/うち国際学会 4件)

1.発表者名

Zhanglin Guo, Tsutomu Miyasaka

2 . 発表標題

CsPbl2Br Perovskite Solar Cells with Voc Over 1.4 $\rm V$

3 . 学会等名

The 8th Conference on Science and Technology of Emerging Solar Energy Materials (国際学会)

4.発表年

2021年

1.発表者名

Zhanglin Guo, Ajay Kumar Jena, Tsutomu Miyasaka

2 . 発表標題

High Voc of all-inorganic CsPbX3 perovskite solar cells

3 . 学会等名

ICYRAM 2022 (国際学会)

4.発表年

2022年

1. 発表者名
Zhanglin Guo, Ajay Kumar Jena, Tsutomu Miyasaka
2.発表標題
VOC over 1.4 V for amorphous tin oxide-based dopant-free CsPbI2Br perovskite solar cells
3.学会等名
Pacifichem 2021 Congress (国際学会)
4.発表年

1 . 発表者名
Tsutomu Miyasaka

2 . 発表標題
Interfacial Engineering for High Voltage (>1.4V) Performance of Inorganic Perovskite Solar Cells

3 . 学会等名
2021 MRS Spring Meeting & Exhibit (招待講演) (国際学会)

4 . 発表年
2021年

〔図書〕 計1件

1.著者名	4.発行年
Ajay K. Jena, Zhanglin Guo, Tsutomu Miyasaka	2022年
2.出版社	5. 総ページ数
Wiley-VCH	48
3 . 書名	
Perovskite Photovoltaics and Optoelectronics: From Fundamentals to Advanced Applications, Chapter 9	
Glapter 9	

〔出願〕 計1件

産業財産権の名称	発明者	権利者
光電変換素子及び発電デバイス	宮坂 力、郭 章林、	同左
	アジェイ クマー	
	ジェナ、武井 出	
産業財産権の種類、番号	出願年	国内・外国の別
特許、特願2021-053883	2021年	国内

〔取得〕 計0件

〔その他〕

5 研究組織

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7.科研費を使用して開催した国際研究集会

〔国際研究集会〕 計0件

8. 本研究に関連して実施した国際共同研究の実施状況

共同研究相手国	相手方研究機関
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